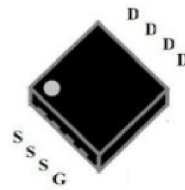
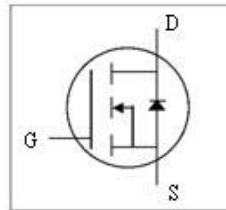


»Features

- Simple Drive Requirement
- Small Size & Low RDS(ON)
- RoHS Compliant & Halogen-Free

BVDSS	30 V
RDS(ON)typ	4.45 mΩ

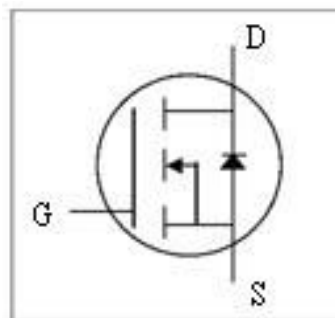


PDFN3*3

»Description

CT03NR005Q is from Coretong innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of The package is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal.

»Schematic & PIN Configuration



PDFN3x3

»Absolute Maximum Ratings@T_J=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Drain Current, V _{GS} @ 10V ₄	40	A
I _D @T _A =25°C	Drain Current, V _{GS} @ 10V ₃	20	A
I _D @T _A =70°C	Drain Current, V _{GS} @ 10V ₃	15.6	A
I _{DM}	Pulsed Drain Current ¹	120	A
P _D @T _A =25°C	Total Power Dissipation ³	3	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

»Thermal Data

Symbol	Parameter	Value	Unit
R _{thj-c}	Maximum Thermal Resistance, Junction-case	4	°C/W
R _{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	40	°C/W

»Electrical Characteristics@T_J=25 °C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =19A	-	4.45	4.8	mΩ
		V _{GS} =4.5V, I _D =12A	-	6.15	7.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.3	2.3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =19A	-	69	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V	-	-	10	μA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =16A	-	11	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	7	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V	-	11	-	ns
t _r	Rise Time	I _D =19A	-	59	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	29	-	ns
t _f	Fall Time	V _{GS} =10V	-	13	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1100	-	pF
C _{oss}	Output Capacitance	V _{DS} =15V	-	350	-	pF
Cr _{ss}	Reverse Transfer Capacitance	f=1.0MHz	-	140	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.1	-	Ω

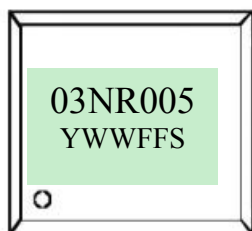
»Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =19A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =20A, V _{GS} =0V	-	15	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	6	-	nC

Notes:

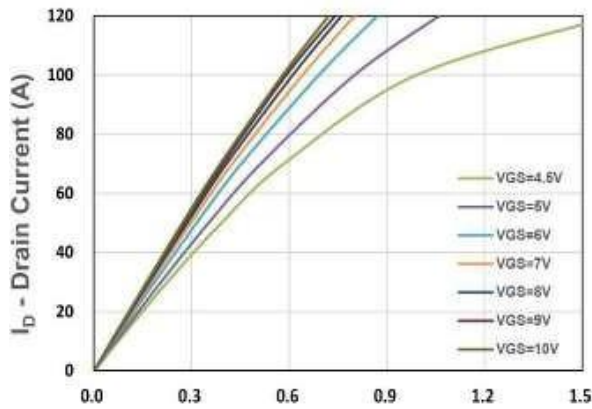
1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² 2oz copper pad of FR4 board, t <10sec ; 135oC/W when mounted on min. copper pad.
4. Maximum current limited by package

»Marking Information

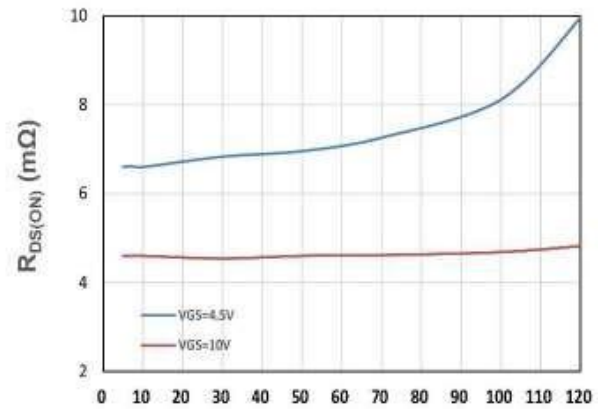


Package	PDFN3x3	
XXXX	Part Number	
PP	Package Code	
Y	Year	F=2020 , G=2021,
WW	Weeks	Ex. 10/27=44weeks, 11/3=45weeks
FF	Wafer lot	Lot No.
S	Serial	Serial No.
Dot	First pin	

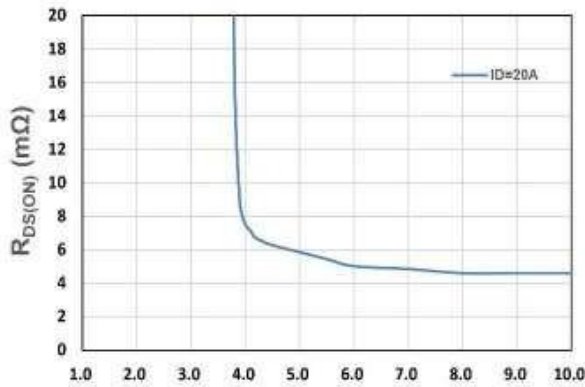
»Typical Characteristics



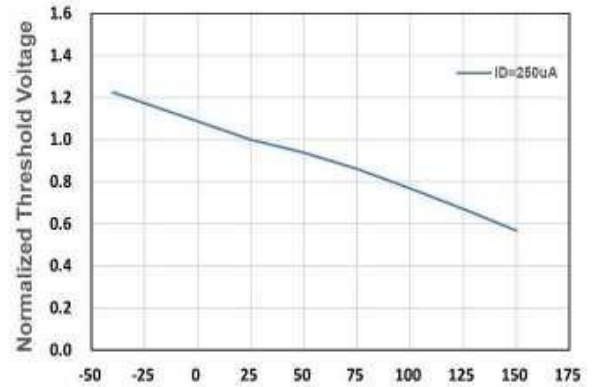
V_{DS} - Drain - Source Voltage (V)
Figure 1. Output Characteristics



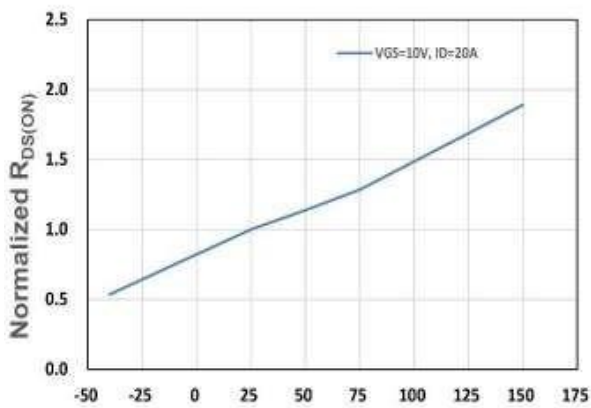
I_D - Drain Current (A)
Figure 2. On-Resistance vs. I_D



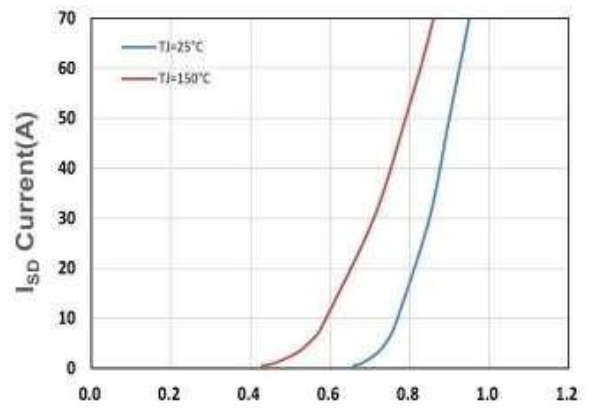
V_{GS} - Gate - Source Voltage (V)
Figure 3. On-Resistance vs. V_{GS}



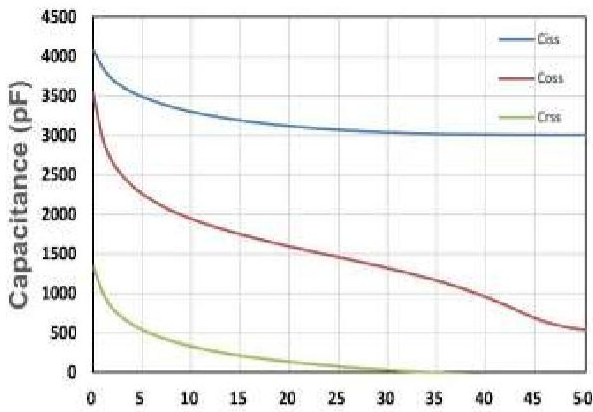
T_j , Junction Temperature(°C)
Figure 4. Gate Threshold Voltage



T_j , Junction Temperature(°C)
Figure 5. Drain-Source On Resistance

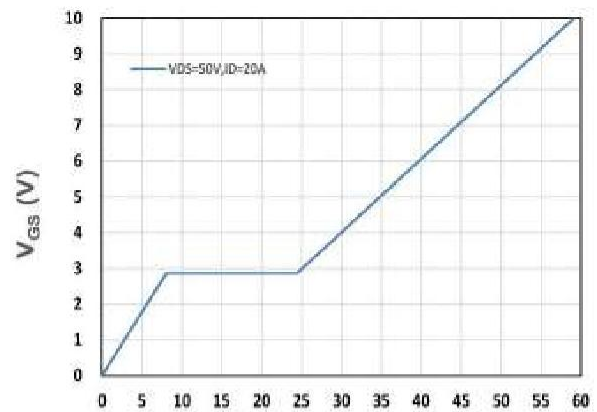


V_{SD} , Source-Drain Voltage(V)
Figure 6. Source-Drain Diode Forward



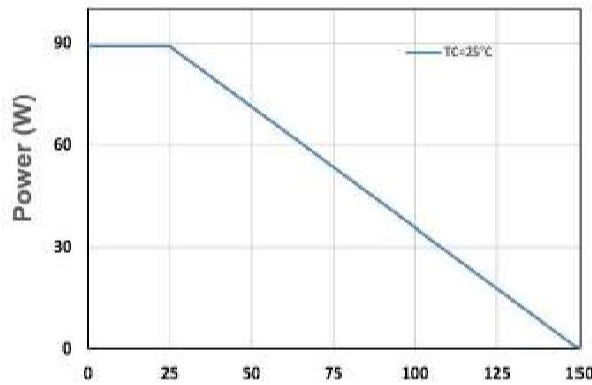
V_{DS} - Drain - Source Voltage (V)

Figure 7. Capacitance



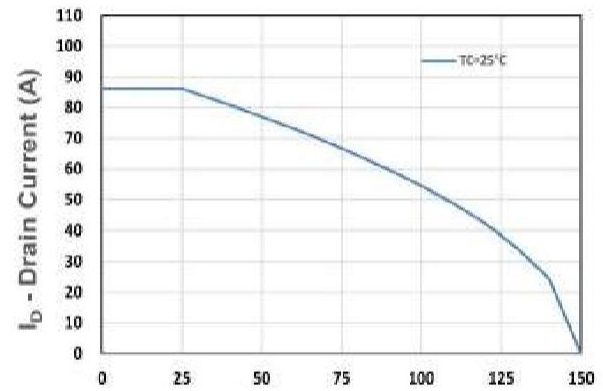
Q_g , Total Gate Charge (nC)

Figure 8. Gate Charge Characteristics



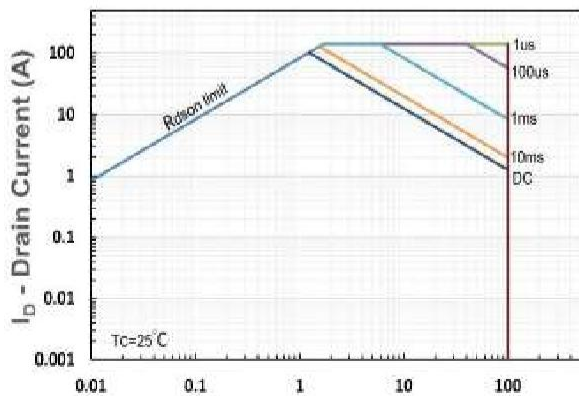
T_j - Junction Temperature (°C)

Figure 9. Power Dissipation



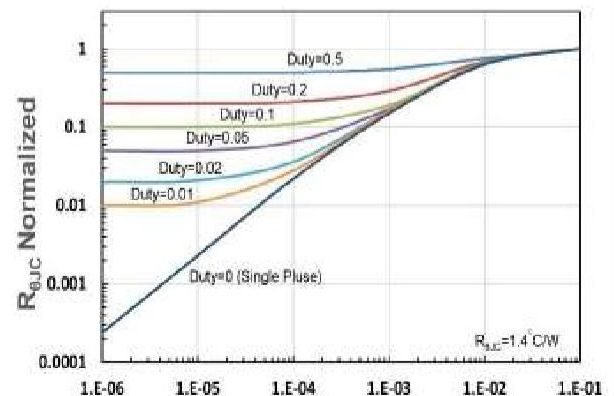
T_j - Junction Temperature (°C)

Figure 10. Drain Current



V_{DS} - Drain-Source Voltage (V)

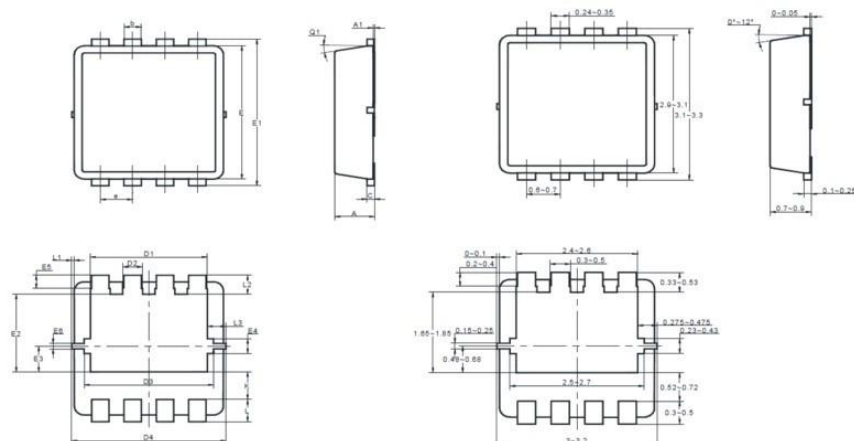
Figure 11. Safe Operating Area



t_1 , Square Wave Pulse Duration(s)

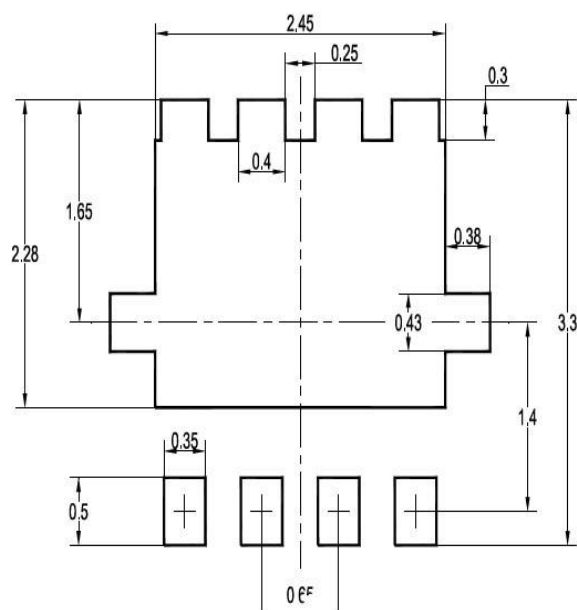
Figure 12. R_{thJC} Transient Thermal Impedance

»Package Outline : PDFN 3x3



UNIT	A	A1	b	c	D1	D2	D3	D4	E	E1	E2	E3	E4
mm	0.9	0.05	0.35	0.25	2.6	0.5	2.7	3.2	3.1	3.3	1.85	0.68	0.43
	0.7	0	0.24	0.1	2.4	0.3	2.5	3	2.9	3.1	1.65	0.48	0.23
UNIT	E5	E6	e	K	L	L1	L2	L3	Ø1				
mm	0.4	0.25	0.7	0.72	0.5	0.1	0.53	0.475	12°				
	0.2	0.15	0.6	0.52	0.3	0	0.33	0.275	0°				

»PDFN 3x3 FOOTPRINT: (mm)



»Ordering information

Order code	Package	Base qty	Delivery mode
CT03NR005Q	PDFN3x3	3k	Tape and reel